MA4X714 (MA714)

Silicon epitaxial planar type

For switching

For wave detection

Features

- Two isolated elements are contained in one package, allowing high-density mounting
- Two MA3X704A (MA704A) is contained in one package (two diodes in a different direction)
- Forward voltage V_F, optimum for low voltage rectification
- Optimum for high frequency rectification because of its short reverse recovery time t_{rr}

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter		Symbol	Rating	Unit	
Reverse voltage		V_R	30	V	
Maximum peak reverse voltage		V_{RM}	30	V	
Peak forward	Single	I_{FM}	150	mA	
current	Series *		110		
Forward current	Single	I_{F}	30	mA	
	Series *		20	101	
Junction temperature		T _j	125	C C	
Storage temperature		T_{stg}	-55 to +125	°C	

Note) *: Value of each diode in series diodes used.

■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

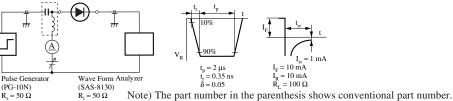
Symbol	Conditions	Min	Тур	Max	Unit
V_{F1}	I _F = 1 mA	60.		0.4	V
V_{F2}	I _F = 30 mA			1.0	
I _R	$V_R = 30 \text{ V}$			1	μΑ
C _t	V _R = 1 V, f = 1 MHz		1.5		pF
t _{rr}	$I_F = I_R = 10 \text{ mA}$		1.0		ns
	$I_{rr} = 1 \text{ mA}, R_L = 100 \Omega$				
η	$V_{IN} = 3 V_{(peak)}$, $f = 30 MHz$		65		%
	$R_L = 3.9 \text{ k}\Omega, C_L = 10 \text{ pF}$				
	V _{F1} V _{F2} I _R C _t t _{rr}	$\begin{array}{ccc} V_{F1} & I_F = 1 \text{ mA} \\ V_{F2} & I_F = 30 \text{ mA} \\ I_R & V_R = 30 \text{ V} \\ C_t & V_R = 1 \text{ V}, f = 1 \text{ MHz} \\ t_{rr} & I_F = I_R = 10 \text{ mA} \\ I_{rr} = 1 \text{ mA}, R_L = 100 \Omega \\ \eta & V_{IN} = 3 \text{ V}_{(peak)}, f = 30 \text{ MHz} \end{array}$	$\begin{array}{cccc} V_{F1} & I_F = 1 \text{ mA} \\ V_{F2} & I_F = 30 \text{ mA} \\ I_R & V_R = 30 \text{ V} \\ C_t & V_R = 1 \text{ V}, f = 1 \text{ MHz} \\ t_{rr} & I_F = I_R = 10 \text{ mA} \\ I_{rr} = 1 \text{ mA}, R_L = 100 \Omega \\ & \eta & V_{IN} = 3 V_{(peak)} \text{ , } f = 30 \text{ MHz} \end{array}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

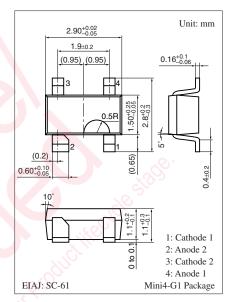
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment. 4. *: t_{rr} measurement circuit

Input Pulse

3. Absolute frequency of input and output is 2 GHz. Bias Application Unit (N-50BU)



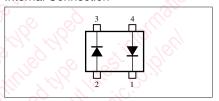


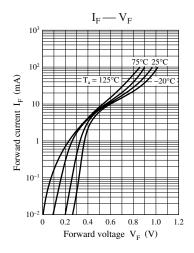
Marking Symbol: M1P

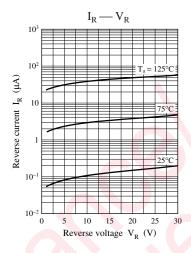
Internal Connection

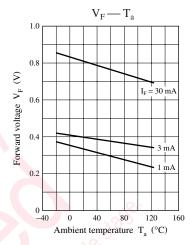
Output Pulse

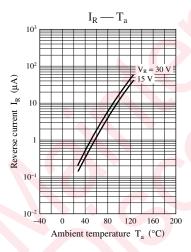
 $I_R = 10 \text{ mA}$ $R_t = 100 \Omega$

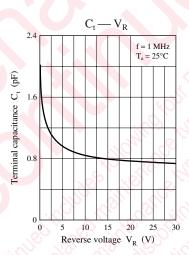












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